

Ultra-Low RDS(on) Power MOSFETs



Features

- AEC-Q101 qualified for reliability
- Advanced split-gate trench (SGT) technology
- technology

 Excellent thermal performance & efficiency
- efficiencyLow RDS(on) minimizes power losses
- High power density packagey
- High junction temperature up to 175°C
- Compact DFN5060 package saves space and material costs

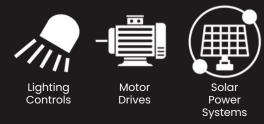


Benefits

Maximize energy efficiency and minimize power losses with RDS(on) as low as 0.8mΩ and exceptional thermal performance.

Ensure reliable operation in demanding conditions and high junction temperatures up to 175°C thanks to AEC-Q101 qualification and robust design.

Applications



Upgrade Auto Performance with MCC's Ultra-Low RDS(on) Power MOSFETs



40V & 60V N-Channel Options in a Compact DFN5060 Package



Upgrade Auto Performance with MCC's Ultra-Low RDS(on) Power MOSFETs in SMA Package



Parametrics & Datasheets:

Product	ТҮРЕ	Package	Drain-Source Voltage (VDS)	Drain-Source On-Resistance RDSON (Max @VGS=10V)	Mounting Type	Datasheet
MCACL220N06YHE3	N-Channel MOSFET	DFN5060	60V	1.6mΩ	Surface Mount	<u>Info</u>
MCACL2D5N06YL	N-Channel MOSFET	DFN5060	60V	2.5mΩ	Surface Mount	<u>Info</u>
MCACL280N04YHE3	N-Channel MOSFET	DFN5060	40V	0.8mΩ	Surface Mount	<u>Info</u>
MCACL330N04YHE3	N-Channel MOSFET	DFN5060	40V	1.0mΩ	Surface Mount	<u>Info</u>

Applications:



- Battery management systems
- Electric power steering
- Seat controls
- Lighting controls



- Electric water pumps
- Motor drives
- DC-DC converters
- Uninterruptible power supplies (UPS)



Solar power systems

CONTACT MCC TO REQUEST A SAMPLE